42P10698D <u>PATENT</u>

IN THE CLAIMS

Please cancel claims 1-16. Attached is a listing of the current claims.

17. (original) A carbon doped oxide film to be formed on a substrate from a carbon

doped oxide precursor in the presence of oxygen.

18. (original) The carbon doped oxide film of claim 17 to act as an inter-layer

dielectric between conductive lines deposited on said substrate following etching of said

carbon doped oxide film.

19. (original) The carbon doped oxide film of claim 17 having a dielectric constant of

less than about 3.0.

20. (original) The carbon doped oxide film of claim 17 formed at a rate exceeding

about 5,620 angstroms per minute on said substrate.

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